N-channel 60 V, 11.5 mOhm, logic level Trench MOSFET in MLPAK33

8 July 2021

Product data sheet

1. General description

General purpose, 42 A rated, logic level N-channel enhancement mode Power MOSFET in MLPAK33 package.

2. Features and benefits

- Logic level compatibility
- Trench MOSFET technology
- Thermally efficient package in a small form factor (3.3 mm x 3.3 mm footprint)

3. Applications

- Secondary side synchronous rectification
- DC-to-DC converters
- Motor drive
- LED lighting
- Load switching
- · Auxiliary control
- Fan control

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 150 °C		-	-	60	V
I _D	drain current	V _{GS} = 10 V; T _{sp} = 25 °C; <u>Fig. 2</u>		-	-	42	Α
P _{tot}	total power dissipation	T _{sp} = 25 °C; <u>Fig. 1</u>		-	-	34.7	W
Tj	junction temperature			-55	-	150	°C
Static chara	acteristics			'		'	
R _{DSon}	drain-source on-state	V_{GS} = 10 V; I_D = 10 A; T_j = 25 °C; <u>Fig. 9</u>		-	9.8	11.5	mΩ
	resistance	$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 9$		-	14	17.6	mΩ
Dynamic ch	naracteristics						
Q _{GD}	gate-drain charge	I _D = 10 A; V _{DS} = 30 V; V _{GS} = 4.5 V;		-	4.3	-	nC
Q _{G(tot)}	total gate charge	T _j = 25 °C; <u>Fig. 11</u> ; <u>Fig. 12</u>		-	9.64	-	nC
Avalanche	ruggedness						
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I _D = 3.5 A; T _{j(init)} = 25 °C; unclamped	[1]	-	-	90	mJ



N-channel 60 V, 11.5 mOhm, logic level Trench MOSFET in MLPAK33

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Source-drain d	iode						
Q _r		$I_S = 10 \text{ A}; \text{ d}I_S/\text{d}t = -100 \text{ A/}\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$ $V_{DS} = 30 \text{ V}; \text{ T}_j = 25 ^{\circ}\text{C}; \frac{\text{Fig. } 15}{\text{C}}$	[2]	-	13	-	nC

- [1] Protected by 100% test
- [2] includes capacitive recovery

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	1 2 3 4	
2	S	source	<u> </u>	
3	S	source		D ⊥
4	G	gate]	
5	D	drain		G—UFIA)
6	D	drain	Laaad	mbb076 S
7	D	drain	8 7 6 5	
8	D	drain	MLPAK33 (SOT8002-1)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PXN012-60QL		plastic thermal enhanced surface mounted package; mini leads; 8 terminals; pitch 0.65 mm; 3.3 x 3.3 x 0.8 mm body	SOT8002-1			

7. Marking

Table 4. Marking codes

Type number	Marking code
PXN012-60QL	7AB

N-channel 60 V, 11.5 mOhm, logic level Trench MOSFET in MLPAK33

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 150 °C		-	60	V
V _{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{sp} = 25 °C; <u>Fig. 1</u>		-	34.7	W
I_D	drain current	V _{GS} = 10 V; T _{sp} = 25 °C; <u>Fig. 2</u>		-	42	Α
		V _{GS} = 10 V; T _{sp} = 100 °C; <u>Fig. 2</u>		-	26	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{sp} = 25 °C$; Fig. 3		-	168	Α
T _{stg}	storage temperature			-55	150	°C
Tj	junction temperature			-55	150	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain	diode					
Is	source current	T _{sp} = 25 °C		-	29	Α
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{sp} = 25 °C		-	168	Α
Avalanche ruç	gedness			'		
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I _D = 3.5 A; T _{j(init)} = 25 °C; unclamped	[1]	-	90	mJ
I _{AS}	non-repetitive avalanche current	$T_{j(init)} = 25 ^{\circ}C$	[1]	-	3.5	A

[1] Protected by 100% test

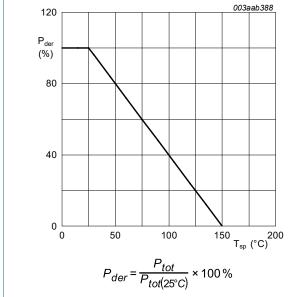


Fig. 1. Normalized total power dissipation as a function of solder point temperature

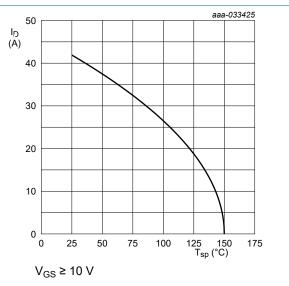
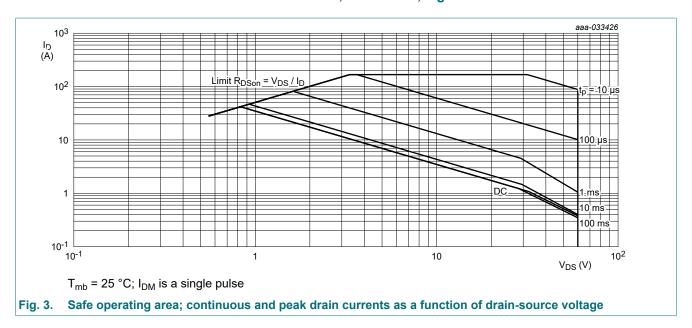


Fig. 2. Continuous drain current as a function of mounting base temperature

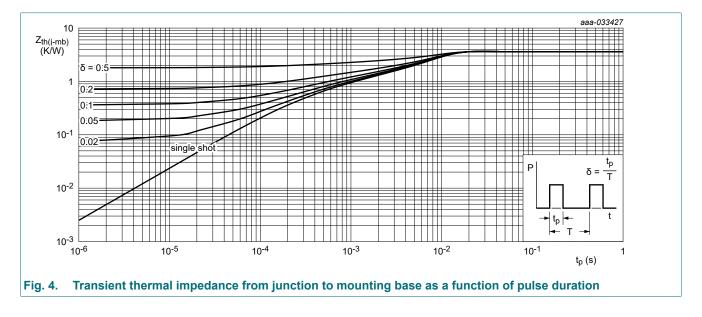
N-channel 60 V, 11.5 mOhm, logic level Trench MOSFET in MLPAK33



9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-sp)}$	thermal resistance from	Fig. 4	-	3	3.6	K/W
0 17	junction to solder point					



N-channel 60 V, 11.5 mOhm, logic level Trench MOSFET in MLPAK33

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	teristics				1	
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	60	70	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	-	64	-	V
V _{GS(th)}	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; Fig. 8$	1.5	1.9	- V 2.9 V - m 1 μ 500 μ 100 n. 100 n. 11.5 m 20 m 17.6 m 30 m	V
	voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.9	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.9	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T _j ≤ 150 °C	-	-4.7	-	mV/K
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	0.01	1	μA
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 150 °C	-	-	500	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100 nA 11.5 mC 20 mC 17.6 mC 30 mC	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; <u>Fig. 9</u>	-	9.8	- \ \ 2.5 \ \ \ 2.9 \ \ \ 2.9 \ \ \ 100 \ \ \ 100 \ \ \ 100 \ \ \ 100 \ \ \ 17.6 \ \ \ 30 \ \ \ - \ \ \ \ \ - \ \ \ \ \ - \ \ \ \ \ \ - \ \ \ \ \ \ - \	mΩ
	resistance	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 150 \text{ °C};$ Fig. 10	-	-	20	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C}; Fig. 9$	-	14	17.6	mΩ
		V_{GS} = 4.5 V; I_D = 10 A; T_j = 150 °C; Fig. 10	-	-	30	mΩ
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	-	1.66	-	Ω
Dynamic cha	racteristics					<u> </u>
Q _{G(tot)}	total gate charge	I _D = 10 A; V _{DS} = 30 V; V _{GS} = 4.5 V; T _j = 25 °C; <u>Fig. 11</u> ; <u>Fig. 12</u>	-	9.64	-	nC
		I _D = 10 A; V _{DS} = 30 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 11</u> ; <u>Fig. 12</u>	-	18.77	-	nC
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 4.5 V; T _j = 25 °C; <u>Fig. 11</u> ; <u>Fig. 12</u>	-	9.54	-	nC
Q _{GS}	gate-source charge	I _D = 10 A; V _{DS} = 30 V; V _{GS} = 4.5 V;	-	3	-	nC
Q _{GS(th)}	pre-threshold gate- source charge	T _j = 25 °C; <u>Fig. 11</u> ; <u>Fig. 12</u>	-	1.6	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	1.4	-	nC
Q_{GD}	gate-drain charge		-	4.3	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I _D = 10 A; V _{DS} = 30 V; T _j = 25 °C; Fig. 11; Fig. 12	-	3.1	-	V
C _{iss}	input capacitance	V _{DS} = 30 V; V _{GS} = 0 V; f = 1 MHz;	-	957	-	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 13</u>	-	386	-	pF
C _{rss}	reverse transfer capacitance		-	31	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 3 \Omega; V_{GS} = 4.5 \text{ V};$	-	8.8	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C$	-	18.5	-	ns
t _{d(off)}	turn-off delay time]	-	12.2	-	ns
t _f	fall time	1	-	10.9	-	ns

N-channel 60 V, 11.5 mOhm, logic level Trench MOSFET in MLPAK33

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Q _{oss}	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 30 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$		-	18	-	nC
Source-drain diode							
V_{SD}	source-drain voltage	$I_S = 10 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; Fig. 14$		-	0.82	1.2	V
t _{rr}	reverse recovery time	$I_S = 10 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;		-	22.1	-	ns
Q _r	recovered charge	V _{DS} = 30 V; T _j = 25 °C; <u>Fig. 15</u>	[1]	-	13	-	nC

[1] includes capacitive recovery

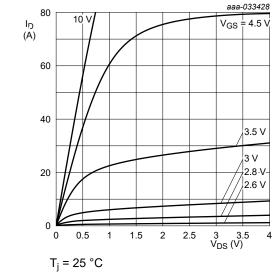


Fig. 5. Output characteristics; drain current as a function of drain-source voltage; typical values

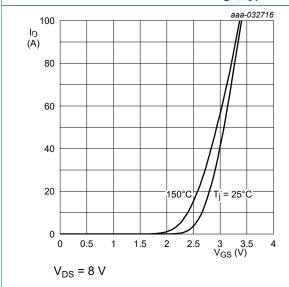


Fig. 7. Transfer characteristics; drain current as a function of gate-source voltage; typical values

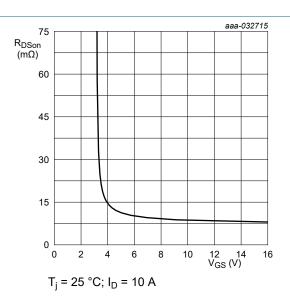


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

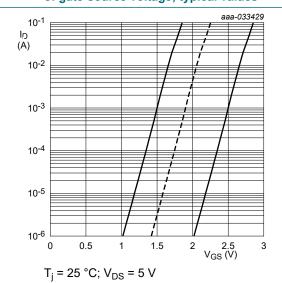


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

N-channel 60 V, 11.5 mOhm, logic level Trench MOSFET in MLPAK33

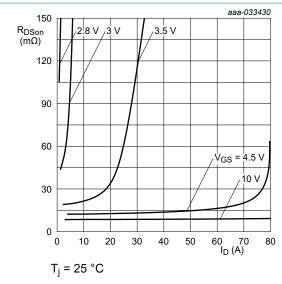


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

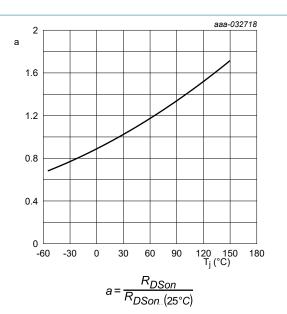


Fig. 10. Normalized drain-source on-state resistance factor as a function of junction temperature

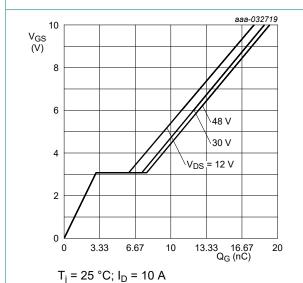


Fig. 11. Gate-source voltage as a function of gate charge; typical values

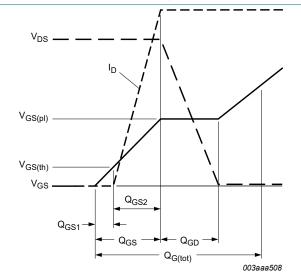


Fig. 12. Gate charge waveform definitions

N-channel 60 V, 11.5 mOhm, logic level Trench MOSFET in MLPAK33

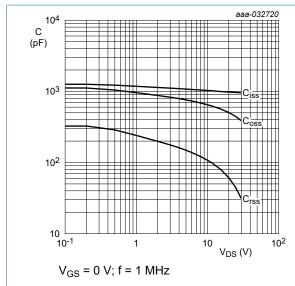
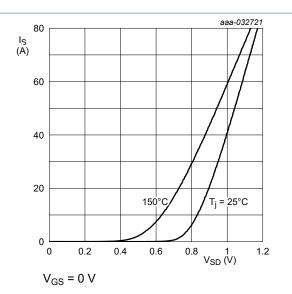


Fig. 13. Input, output and reverse transfer capacitances | Fig. 14. Source-drain (diode forward) current as a as a function of drain-source voltage; typical values



function of source-drain (diode forward) voltage; typical values

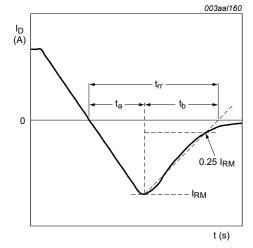


Fig. 15. Reverse recovery timing definition

N-channel 60 V, 11.5 mOhm, logic level Trench MOSFET in MLPAK33

11. Package outline

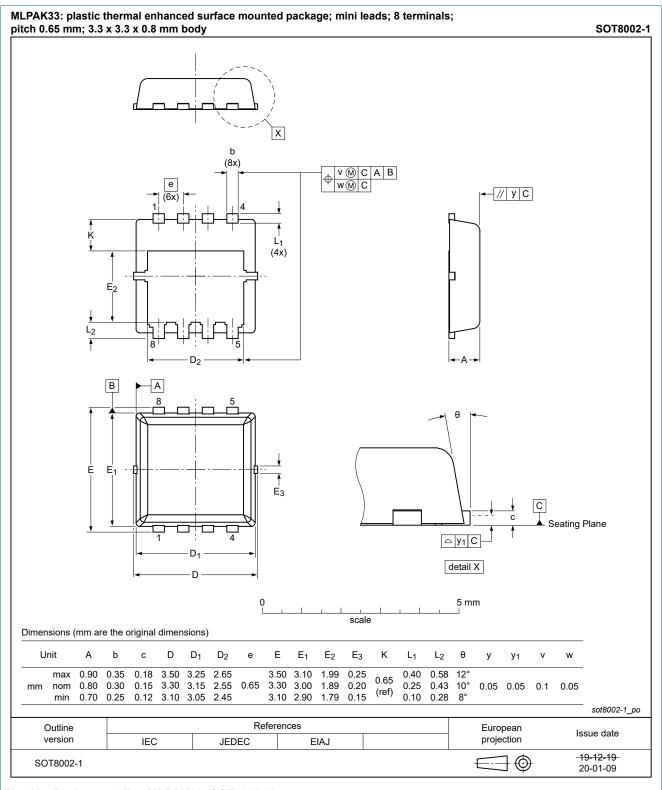
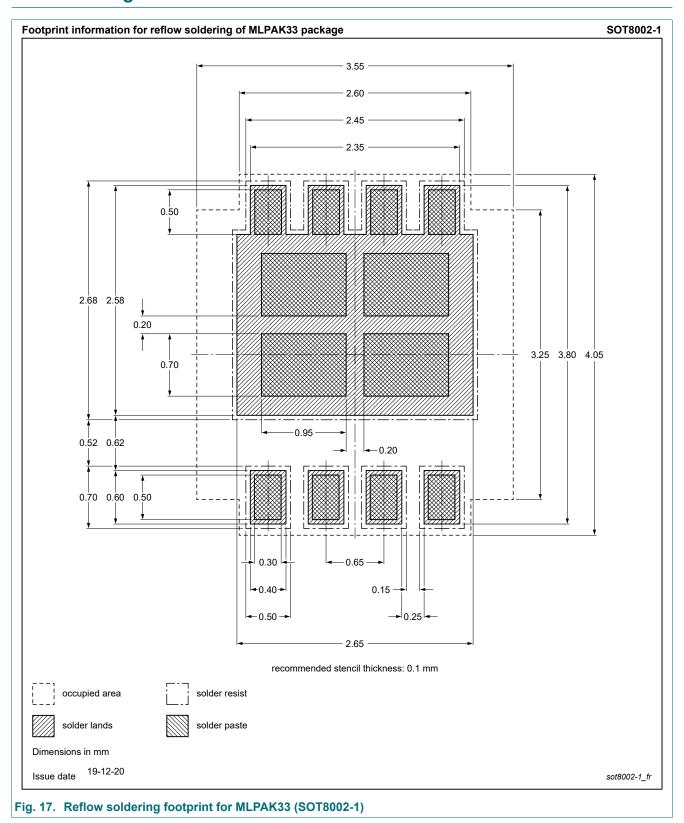


Fig. 16. Package outline MLPAK33 (SOT8002-1)

N-channel 60 V, 11.5 mOhm, logic level Trench MOSFET in MLPAK33

12. Soldering



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13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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N-channel 60 V, 11.5 mOhm, logic level Trench MOSFET in MLPAK33

Contents

4 0	Namanal daganintian	4
1. G	General description	1
2. F	eatures and benefits	1
3. A	Applications	1
4. Q	Quick reference data	1
5. P	inning information	2
6. O	Ordering information	2
7. N	Marking	2
8. L	imiting values	3
9. T	hermal characteristics	4
10.	Characteristics	5
11.	Package outline	9
12.	Soldering	. 10
	Legal information	

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